

Nils Nordell

List of Publications by Citations

Source: <https://exaly.com/author-pdf/4382161/nils-nordell-publications-by-citations.pdf>

Version: 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

59
papers

1,868
citations

19
h-index

42
g-index

60
ext. papers

2,027
ext. citations

2.3
avg, IF

3.66
L-index

#	Paper	IF	Citations
59	Deep Defect Centers in Silicon Carbide Monitored with Deep Level Transient Spectroscopy. <i>Physica Status Solidi A</i> , 1997 , 162, 199-225		330
58	Ionization rates and critical fields in 4H silicon carbide. <i>Applied Physics Letters</i> , 1997 , 71, 90-92	3.4	319
57	Deep level defects in electron-irradiated 4H SiC epitaxial layers. <i>Journal of Applied Physics</i> , 1997 , 81, 6155-6159	2.4	241
56	Surface roughening in ion implanted 4H-silicon carbide. <i>Journal of Electronic Materials</i> , 1999 , 28, 214-218	1.9	86
55	Study of avalanche breakdown and impact ionization in 4H silicon carbide. <i>Journal of Electronic Materials</i> , 1998 , 27, 335-341	1.9	81
54	Electrically active point defects in n-type 4H SiC. <i>Journal of Applied Physics</i> , 1998 , 84, 1354-1357	2.5	64
53	Electrical properties of the titanium acceptor in silicon carbide. <i>Physical Review B</i> , 1997 , 55, 13618-13624	3.3	59
52	Investigation of aluminum nitride grown by metalorganic chemical-vapor deposition on silicon carbide. <i>Journal of Applied Physics</i> , 1997 , 82, 2990-2995	2.5	55
51	Transient enhanced diffusion of implanted boron in 4H-silicon carbide. <i>Applied Physics Letters</i> , 2000 , 76, 1434-1436	3.4	44
50	Design and Performance of a New Reactor for Vapor Phase Epitaxy of 3C, 6H, and 4H SiC. <i>Journal of the Electrochemical Society</i> , 1996 , 143, 2910-2919	3.9	34
49	Temperature dependence of avalanche breakdown for epitaxial diodes in 4H silicon carbide. <i>Applied Physics Letters</i> , 1998 , 73, 1850-1852	3.4	30
48	Influence of growth conditions on electrical characteristics of AlN on SiC. <i>Applied Physics Letters</i> , 1997 , 70, 3549-3551	3.4	29
47	Diffusion of Zn and Mg in AlGaAs/GaAs structures grown by metalorganic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , 1990 , 67, 778-786	2.5	29
46	Ionization Rates and Critical Fields in 4H SiC Junction Devices. <i>Materials Science Forum</i> , 1998 , 264-268, 513-516	0.4	24
45	Temperature stable Pd ohmic contacts to p-type 4H-SiC formed at low temperatures. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 605-611	2.9	24
44	Growth of SiC using hexamethyldisilane in a hydrogen-poor ambient. <i>Applied Physics Letters</i> , 1994 , 64, 1647-1649	3.4	23
43	Characterization of electrically active deep level defects in 4H and 6H SiC. <i>Diamond and Related Materials</i> , 1997 , 6, 1388-1391	3.5	21

42	Influence of H ₂ Addition and Growth Temperature on CVD of SiC Using Hexamethyldisilane and Ar. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 565-571	3.9	21
41	Improved InP regrowth properties in metalorganic vapor phase epitaxy by addition of CCl ₄ . <i>Applied Physics Letters</i> , 1992 , 61, 22-24	3.4	21
40	Control of Al and B doping transients in 6H and 4H SiC grown by vapor phase epitaxy. <i>Journal of Electronic Materials</i> , 1997 , 26, 187-192	1.9	19
39	Investigation of surface recombination and carrier lifetime in 4H/6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 239-243	3.1	19
38	MOVPE growth of InP around reactive ion etched mesas. <i>Journal of Crystal Growth</i> , 1991 , 114, 92-98	1.6	18
37	Hall effect investigations of 4H-SiC epitaxial layers grown on semi-insulating and conducting substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 389-394	3.1	17
36	Influence of MOVPE growth conditions and CCl ₄ addition on InP crystal shapes. <i>Journal of Crystal Growth</i> , 1992 , 125, 597-611	1.6	15
35	Thermostable Ohmic Contacts on p-Type SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 787-790	0.4	14
34	Capacitance transient studies of electron irradiated 4H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 336-339	3.1	13
33	Diffusion of light elements in 4H and 6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 275-280	3.1	13
32	Bistable switching in nonlinear Al _{0.06} Ga _{0.94} As Balons. <i>Applied Physics Letters</i> , 1988 , 53, 1785-1787	3.4	13
31	Incorporation of the D-Center in SiC Controlled either by Coimplantation of Si/B and C/B or by Site-Competition Epitaxy. <i>Materials Science Forum</i> , 1998 , 264-268, 681-684	0.4	12
30	Low-power optical bistability in a thermally stable AlGaAs Balon. <i>Applied Physics Letters</i> , 1989 , 54, 2290-2292	3.4	12
29	Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy. <i>Diamond and Related Materials</i> , 1997 , 6, 1293-1296	3.5	11
28	Scanning capacitance microscopy investigations of SiC structures. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 209-211	4.3	11
27	Electric-field-assisted migration and accumulation of hydrogen in silicon carbide. <i>Physical Review B</i> , 2000 , 61, 7195-7198	3.3	11
26	Formation of precipitates in heavily boron doped 4H-SiC. <i>Applied Surface Science</i> , 2006 , 252, 5316-5320	6.7	10
25	Transmission Electron Microscopy Investigation of Defects in B-Implanted 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 413-416	0.4	10

24	MOVPE regrowth of semi-insulating InP around reactive ion etched laser mesas. <i>Electronics Letters</i> , 1991 , 27, 926-927	1.1	10
23	Comparison of SiO ₂ and AlN as Gate Dielectric for SiC MOS Structures. <i>Materials Science Forum</i> , 1998 , 264-268, 877-880	0.4	9
22	Equilibrium crystal shapes for 6H AND 4H SiC grown on non-planar substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 130-134	3.1	8
21	Study of the electrical, thermal and chemical properties of Pd ohmic contacts to p-type 4H-SiC: dependence on annealing conditions. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 291-295	3.1	8
20	Dissociation Energy of the Passivating Hydrogen-Aluminum Complex in 4H-SiC. <i>Materials Science Forum</i> , 2001 , 353-356, 427-430	0.4	7
19	Homoepitaxy of 6H and 4H SiC on nonplanar substrates. <i>Applied Physics Letters</i> , 1998 , 72, 197-199	3.4	7
18	Theory and Realization of a Two - Layer Hall Effect Measurement Concept for Characterization of Epitaxial and Implanted Layers of SiC. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 423, 661		7
17	High-voltage operation of field-effect transistors in silicon carbide. <i>IEEE Electron Device Letters</i> , 1997 , 18, 521-522	4.4	6
16	Polytype homogeneity and doping distribution in homoepitaxial 4H SiC grown on nonplanar substrates. <i>Applied Physics Letters</i> , 2002 , 80, 1755-1757	3.4	6
15	AFM Study of In Situ Etching of 4H and 6H SiC Substrates. <i>Materials Science Forum</i> , 1998 , 264-268, 363-366	4	6
14	B implantation in 6H SiC: Lattice damage recovery and implant activation upon high-temperature annealing. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1040		5
13	Epitaxial growth of SiC in a new multi-wafer VPE reactor. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 143-146	3.1	5
12	Growth and performance of AlGaAs/GaAs heterostructure bipolar transistors. <i>Journal of Crystal Growth</i> , 1991 , 107, 909-914	1.6	5
11	Boron implantation and epitaxial regrowth studies of 6H SiC. <i>Journal of Electronic Materials</i> , 1998 , 27, 833-837	1.9	4
10	Al/Si Ohmic Contacts to p-Type 4H-SiC for Power Devices. <i>Materials Science Forum</i> , 2000 , 338-342, 1009-1012	1.1	4
9	Ground States of the Ionized Isoelectronic Ti Acceptor in SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 537-540	0.4	4
8	Epitaxial Growth of SiC on Ion-Beam Synthesized SiC: Structural Characterization. <i>Materials Science Forum</i> , 2000 , 338-342, 309-312	0.4	3
7	Growth of 4H and 6H SiC Trenches and Around Stripe Mesas. <i>Materials Science Forum</i> , 1998 , 264-268, 131-134	0.4	3

6	Deuterium Incorporation in Acceptor Doped Epitaxial Layers of 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 761-764	0.4	3
5	Design and Performance of a New Reactor for Metal Organic Vapor Phase Epitaxial Growth of Extremely Uniform Layers. <i>Journal of the Electrochemical Society</i> , 1992 , 139, 583-590	3.9	3
4	Observation of near-surface electrically active defects in n-type 6H-SiC. <i>Journal of Applied Physics</i> , 1998 , 83, 3649-3651	2.5	1
3	Electrical Activation of B Implant in 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 705-708	0.4	
2	6H-SiC Crystallinity Behaviour upon B Implantation Studied by Raman Scattering. <i>Materials Science Forum</i> , 1998 , 264-268, 741-744	0.4	
1	SiC Surface Engineering for High Voltage JFET Applications. <i>Materials Science Forum</i> , 1998 , 264-268, 1081-1084	0.4	